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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10014949	FILING DATE 10/26/2001	CLASS 257	SUBCLASS 257	GAU 2811	EXAMINER S RAO
**APPLICANTS: Yamamoto Makoto; Iwabuchi Akio;					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED: JAPAN P2001-128187 04/25/2001					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO	
Verified and Acknowledged Examiners's initials		44471-265522 (13700)			
TITLE : Later: I transistor having graded base region, semiconductor integrated circuit and fabrication method thereof					

U.S. DEPT. OF COMM./PAT. & TM.-PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		Primary Examiner	DRAWING	
Amount Due	Date Paid		Sheets Drwg.	Figs. Drwg.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner	
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